

IN THE SPECIFICATION

Please replace the paragraph beginning at page 6, line 18, with the following:

Referring to FIG. 13, the third hard mask (590 of FIG. 12) is patterned by dry etching using the photoresist pattern (12 of FIG. 12) as an etch mask, thereby forming a third hard ~~mask 691~~ mask 591. Thereafter, the first photoresist pattern 910 is removed if necessary.

Please replace the paragraph beginning at page 10, line 1, with the following:

There are many ~~way~~ ways to practice the invention. What follows are descriptions of example, non-limiting, embodiments of the invention.